

MMBT5551M3

NPN High Voltage Transistor

The MMBT5551M3 device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose high voltage applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	160	Vdc
Collector–Base Voltage	V_{CBO}	180	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	60	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	265 2.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	640 5.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

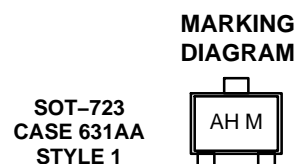
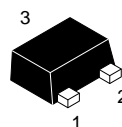
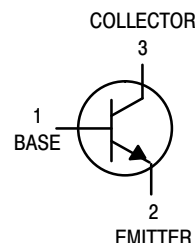
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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AH = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT5551M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSVMMBT5551M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 3) (I _C = 1.0 mA, I _B = 0)	V _{(BR)CEO}	160	–	Vdc
Collector–Base Breakdown Voltage (I _C = 100 μA, I _E = 0)	V _{(BR)CBO}	180	–	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 μA, I _C = 0)	V _{(BR)EBO}	6.0	–	Vdc
Collector Cutoff Current (V _{CB} = 120 Vdc, I _E = 0) (V _{CB} = 120 Vdc, I _E = 0, T _A = 100°C)	I _{CBO}	–	100	nA μA
Emitter Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	–	50	nA
ON CHARACTERISTICS				
DC Current Gain (I _C = 1.0 mA, V _{CE} = 5.0 Vdc) (I _C = 10 mA, V _{CE} = 5.0 Vdc) (I _C = 50 mA, V _{CE} = 5.0 Vdc)	h _{FE}	80 80 30	– 250 –	–
Collector–Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 50 mA, I _B = 5.0 mA)	V _{CE(sat)}	– –	0.15 0.20	Vdc
Base–Emitter Saturation Voltage (I _C = 10 mA, I _B = 1.0 mA) (I _C = 50 mA, I _B = 5.0 mA)	V _{BE(sat)}	– –	1.0 1.0	Vdc
Collector Emitter Cut-off (V _{CB} = 10 V) (V _{CB} = 75 V)	I _{CES}	– –	50 100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

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TYPICAL CHARACTERISTICS

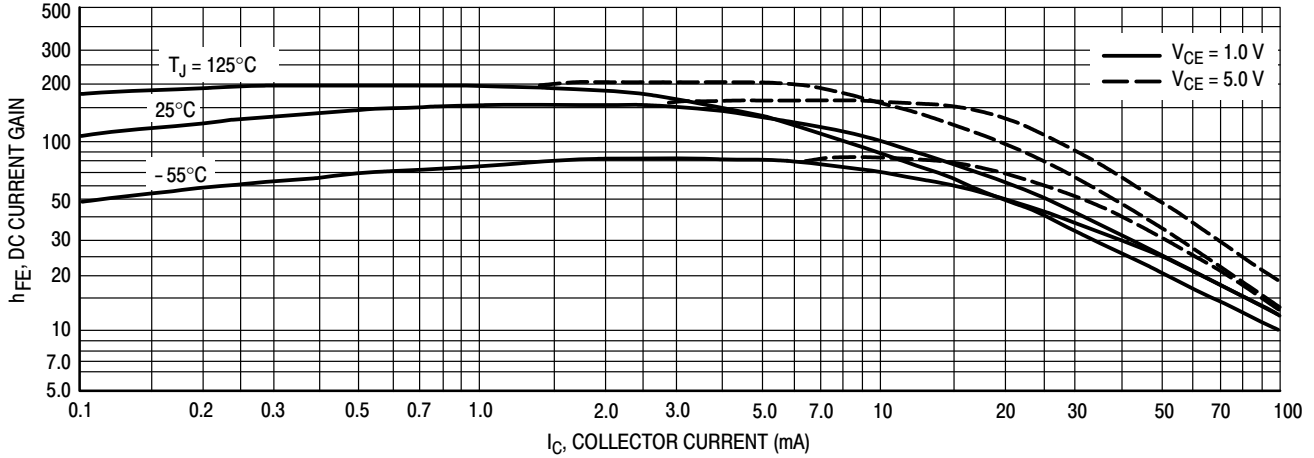


Figure 1. DC Current Gain

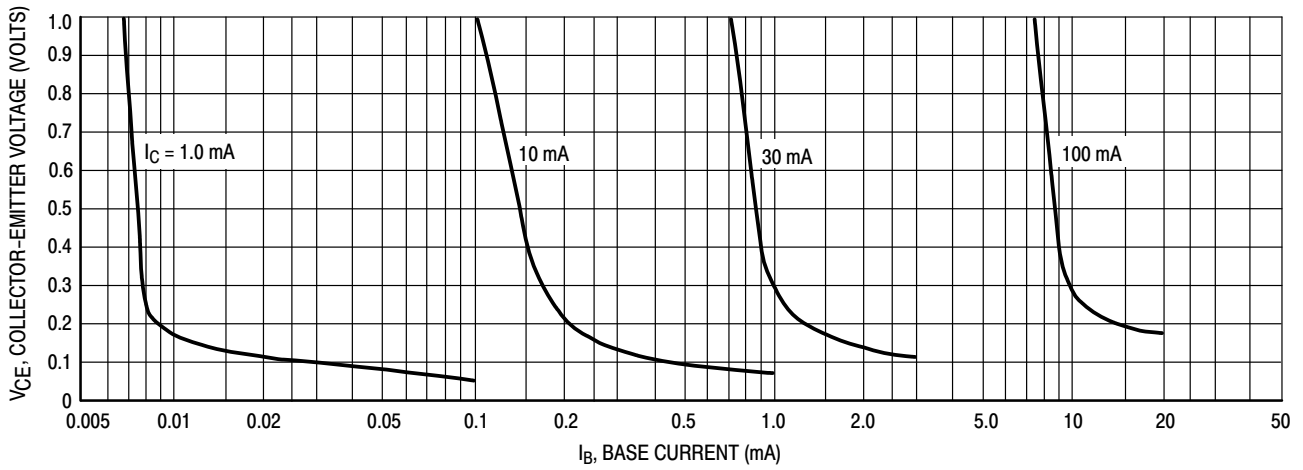


Figure 2. Collector Saturation Region

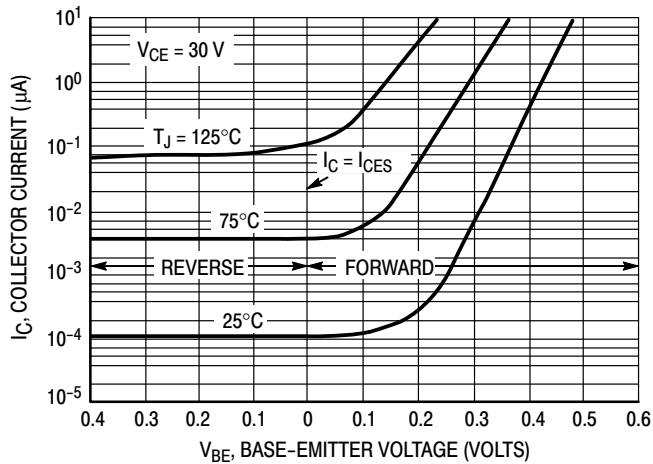


Figure 3. Collector Cut-Off Region

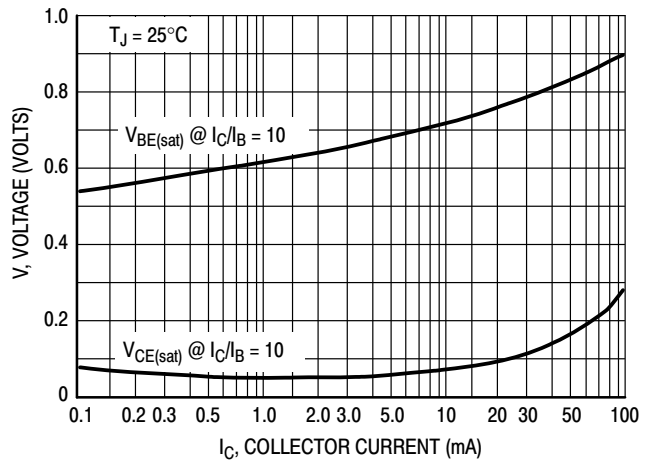
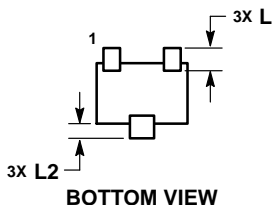
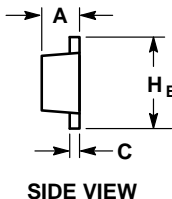
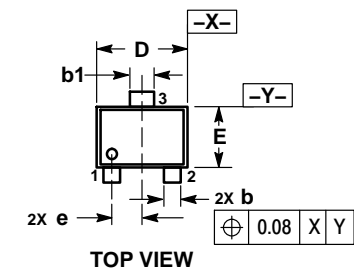


Figure 4. "On" Voltages

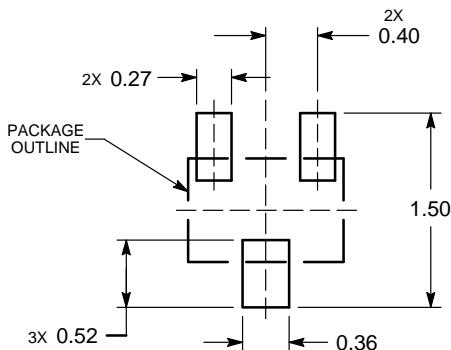
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PACKAGE DIMENSIONS

SOT-723
CASE 631AA
ISSUE D



RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

NOTES:


1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 1:

1. BASE
2. EMITTER
3. COLLECTOR

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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